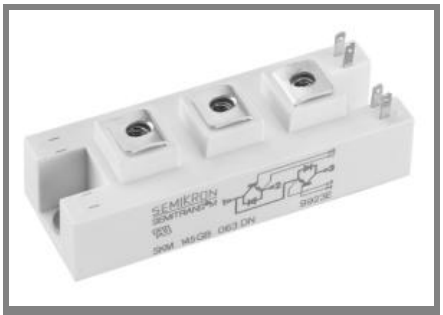
SKM 100GB125DN



SEMITRANS® 2N

Ultra Fast IGBT Module

SKM 100GB125DN

Features

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- Low inductance case
- Short tail current with low temperature dependence
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- Switched mode power supplies at f_{sw} > 20 kHz
- Resonant inverters up to 100 kHz
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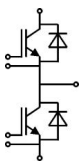
- Electronic welders at f_{sw} > 20 kHz



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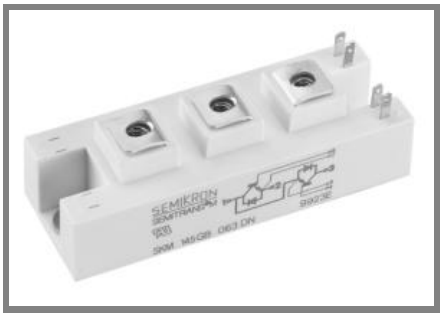
Absolute Maximum Ratings			T_c = 25 °C, unless otherwise specified	
Symbol	**Conditions**		**Values**	**Units**
IGBT				
V_{CES}	T_j = 25 °C		1200	V
I_C	T_j = 150 °C	T_{case} = 25 °C	100	A
		T_{case} = 85 °C	80	A
I_{CRM}	I_{CRM}=2xI_{Cnom}		150	A
V_{GES}			± 20	V
t_{psc}	V_{CC} = 600 V; $V_{GE} \leq$ 20 V; V_{CES} < 1200 V	T_j = 125 °C	10	µs
Inverse Diode				
I_F	T_j = 150 °C	T_{case} = 25 °C	95	A
		T_{case} = 80 °C	65	A
I_{FRM}	I_{FRM}=2xI_{Fnom}		150	A
I_{FSM}	t_p = 10 ms; sin.	T_j = 150 °C	720	A
Module				
$I_{t(RMS)}$			200	A
T_{vj}			- 40 ... + 150	°C
T_{stg}			125	°C
V_{isol}	AC, 1 min.		4000	V

Characteristics			T_c = 25 °C, unless otherwise specified			
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
IGBT						
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 2 mA		4,5	5,5	6,5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T_j = 25 °C		0,15	0,45	mA
		T_j = 125 °C				mA
V_{CE0}		T_j = 25 °C				V
		T_j = 125 °C				V
r_{CE}	V_{GE} = 15 V	T_j = 25°C				mΩ
		T_j = 125°C				mΩ
$V_{CE(sat)}$	I_{Cnom} = 75 A, V_{GE} = 15 V	T_j = °$C_{chiplev.}$		3,3	3,85	V
C_{ies}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		5	6,6	nF
C_{oes}				0,72	0,9	nF
C_{res}				0,38	0,5	nF
Q_G	V_{GE} = 0 - +20V			650		nC
R_{Gint}	T_j = °C			5		Ω
$t_{d(on)}$	R_{Gon} = 8 Ω	V_{CC} = 600V		80		ns
t_r		I_C= 75A		40		ns
E_{on}		T_j = 125 °C		9		mJ
$t_{d(off)}$	R_{Goff} = 8 Ω	V_{GE} = ± 15V		360		ns
t_f				20		ns
E_{off}				3,5		mJ
$R_{th(j-c)}$	per IGBT				0,18	K/W

SKM 100GB125DN



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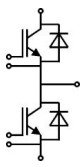

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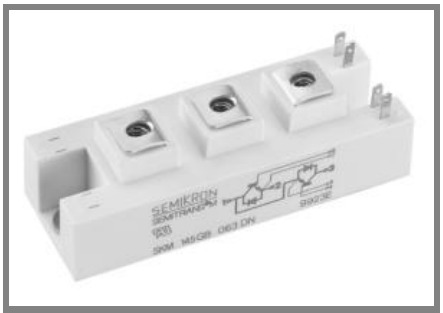
Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
Inverse Diode						
$V_F = V_{EC}$	I_{Fnom} = 75 A; V_{GE} = 0 V	T_j = 25 °$C_{chiplev.}$		2	2,5	V
		T_j = 125 °$C_{chiplev.}$		1,8		V
V_{F0}		T_j = °C		1,1	1,2	V
r_F		T_j = °C		12	17,3	mΩ
I_{RRM}	I_F = 75 A	T_j = 125 °C		50		A
Q_{rr}	di/dt = 800 A/µs			11,5		µC
E_{rr}	V_{GE} = 0 V; V_{CC} = 600 V					mJ
$R_{th(j-c)D}$	per diode				0,5	K/W
Module						
L_{CE}				20	25	nH
$R_{CC'+EE'}$	res., terminal-chip	T_{case}= 25 °C		0,75		mΩ
		T_{case}= 125 °C		1		mΩ
$R_{th(c-s)}$	per module				0,05	K/W
M_s	to heat sink M6		3		5	Nm
M_t	to terminals M5		2,5		5	Nm
w					160	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.



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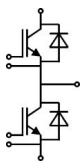

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Z_{th} Symbol	Conditions	Values	Units
$Z_{th(j-c)I}$			
R_i	i = 1	95	mk/W
R_i	i = 2	65	mk/W
R_i	i = 3	17,5	mk/W
R_i	i = 4	2,5	mk/W
tau_i	i = 1	0,0327	s
tau_i	i = 2	0,008	s
tau_i	i = 3	0,0017	s
tau_i	i = 4	0,008	s
$Z_{th(j-c)D}$			
R_i	i = 1	300	mk/W
R_i	i = 2	160	mk/W
R_i	i = 3	36	mk/W
R_i	i = 4	4	mk/W
tau_i	i = 1	0,054	s
tau_i	i = 2	0,001	s
tau_i	i = 3	0,0015	s
tau_i	i = 4	0,1	s

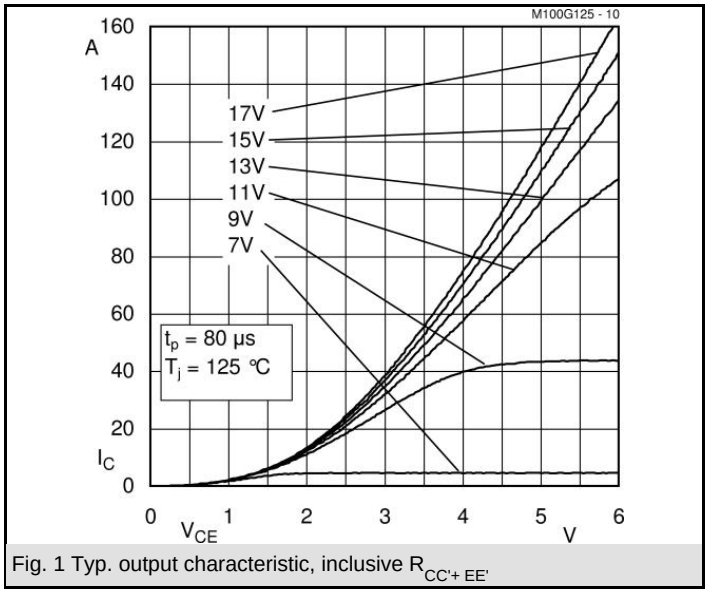


Fig. 1 Typ. output characteristic, inclusive $R_{CC'+EE'}$

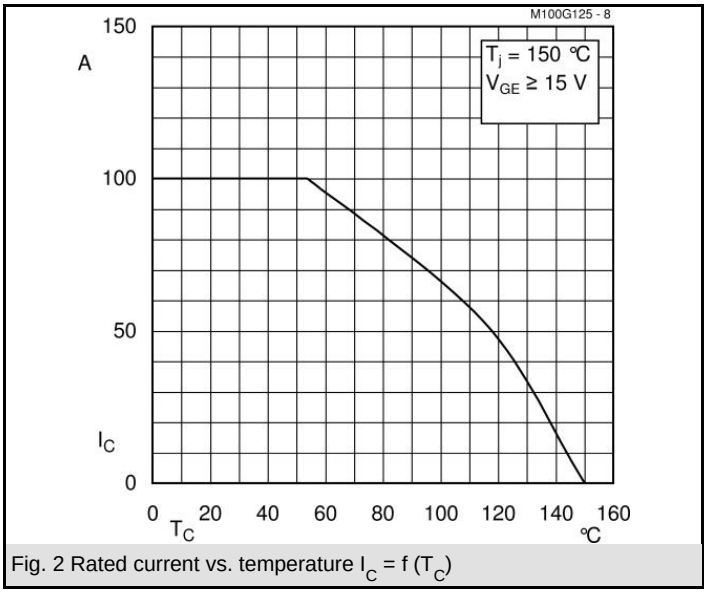


Fig. 2 Rated current vs. temperature $I_C = f(T_C)$

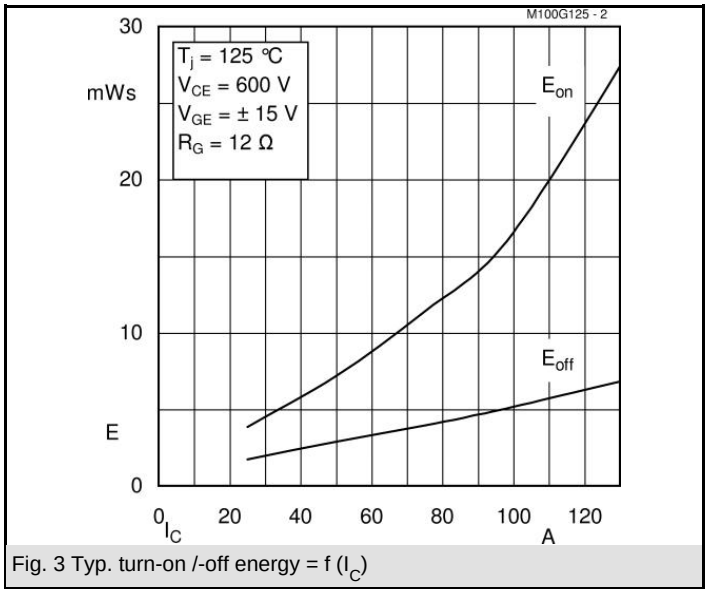


Fig. 3 Typ. turn-on /-off energy = f (I_C)

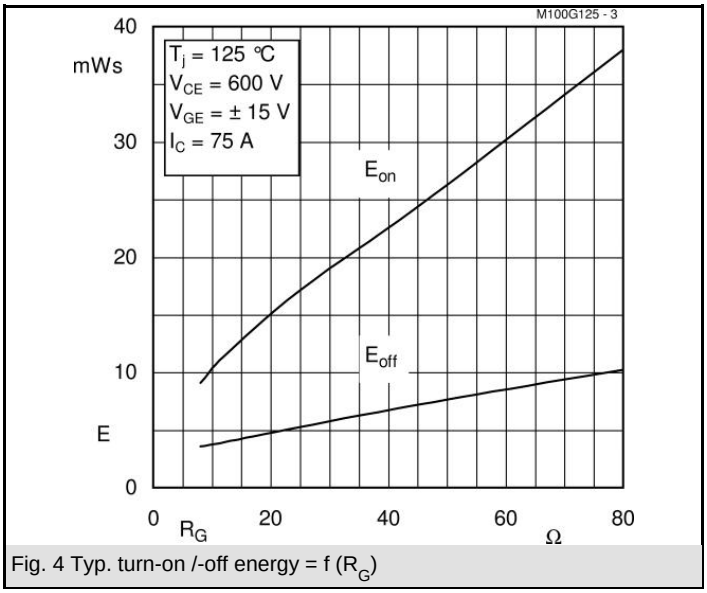


Fig. 4 Typ. turn-on /-off energy = f (R_G)

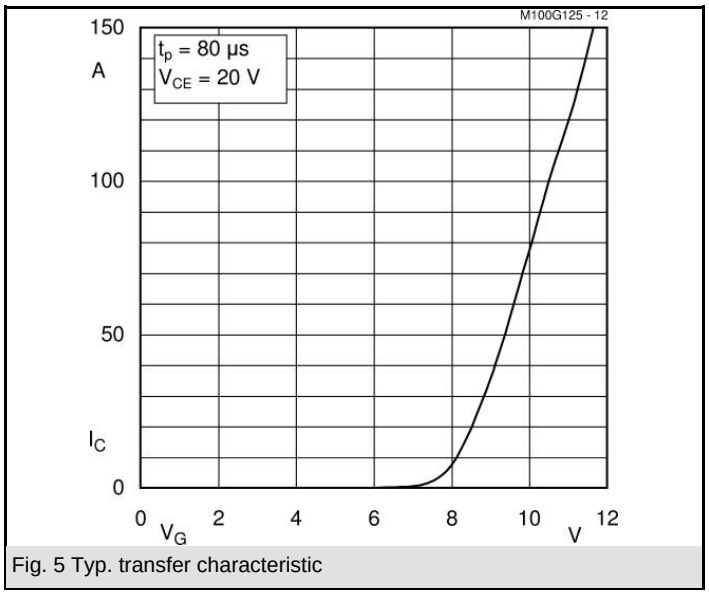


Fig. 5 Typ. transfer characteristic

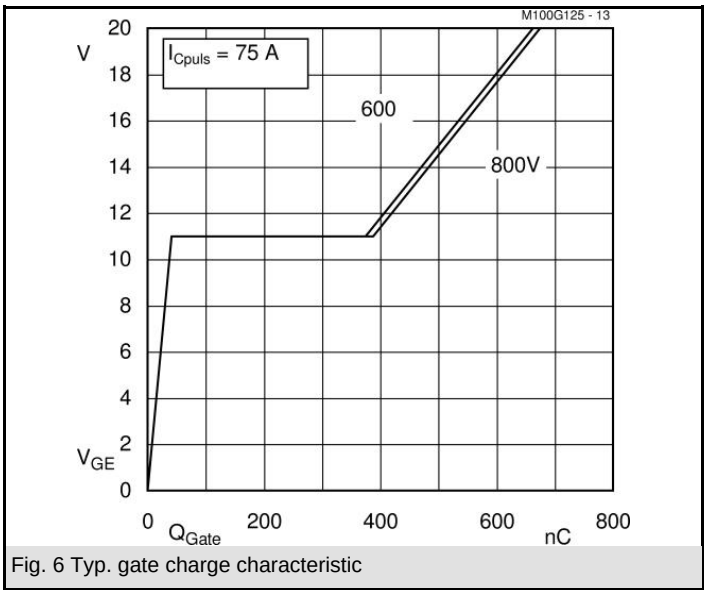


Fig. 6 Typ. gate charge characteristic

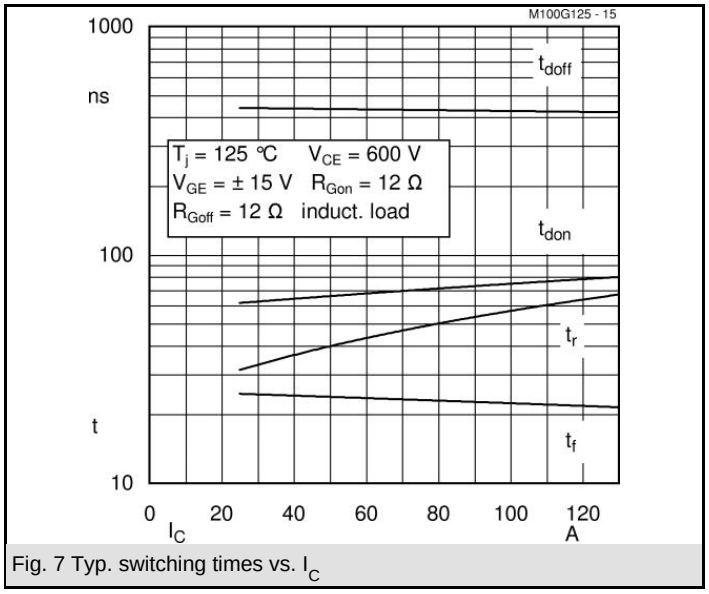


Fig. 7 Typ. switching times vs. I_C

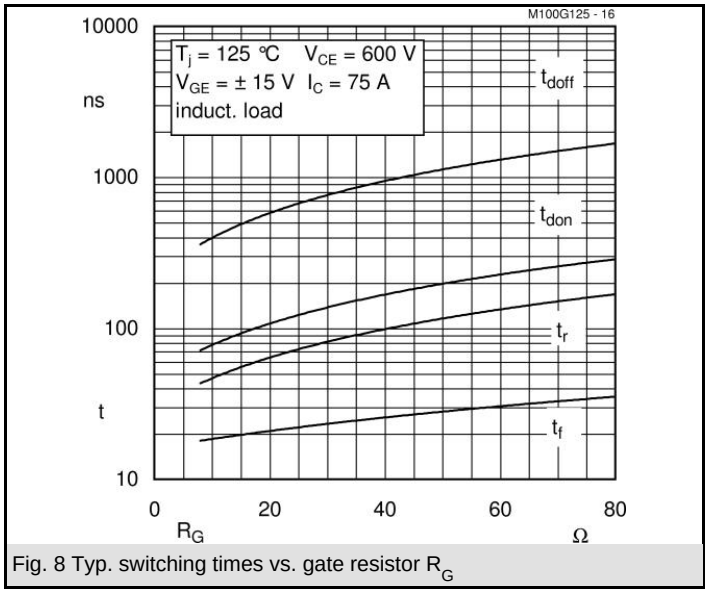


Fig. 8 Typ. switching times vs. gate resistor R_G

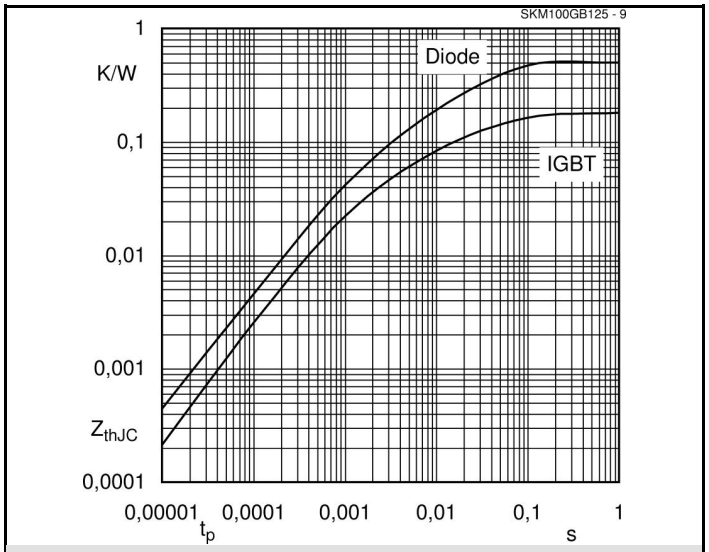


Fig. 9 Transient thermal impedance

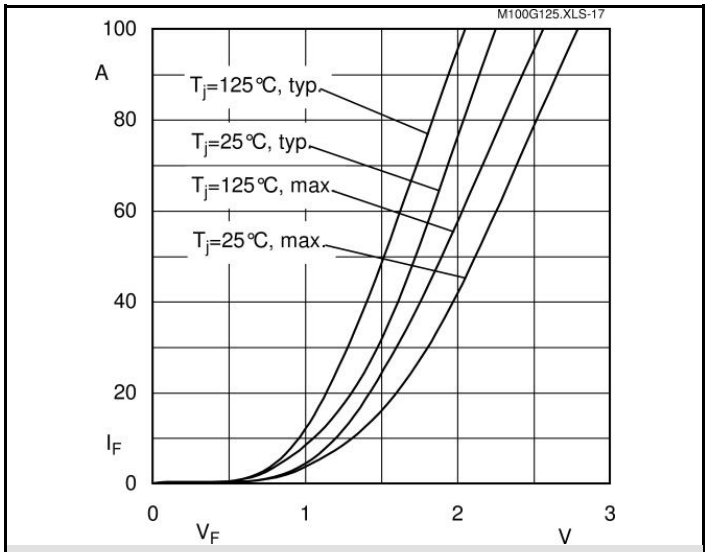


Fig. 10 CAL diode forward characteristic

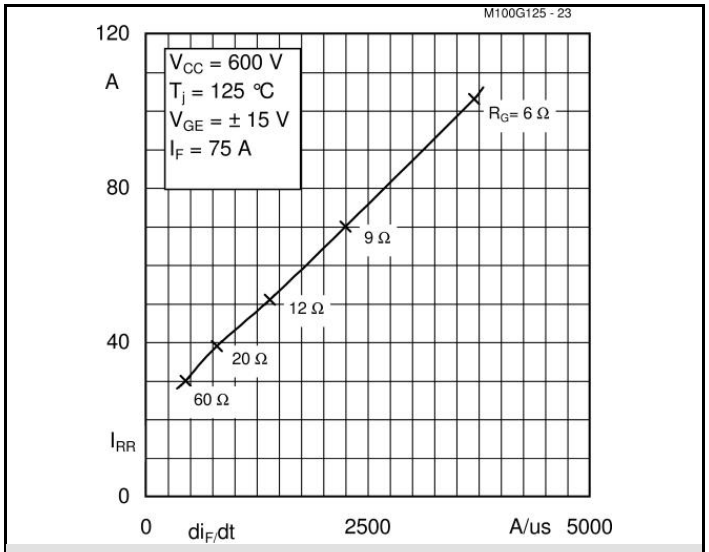


Fig. 11 Typ. CAL diode peak reverse recovery current

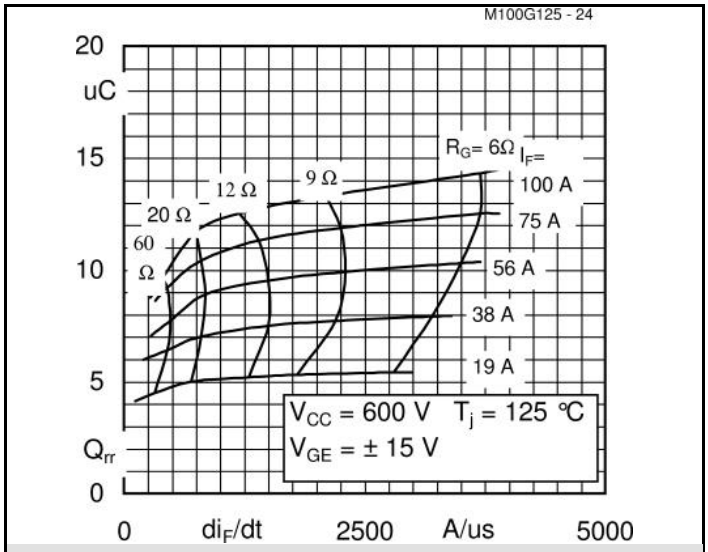
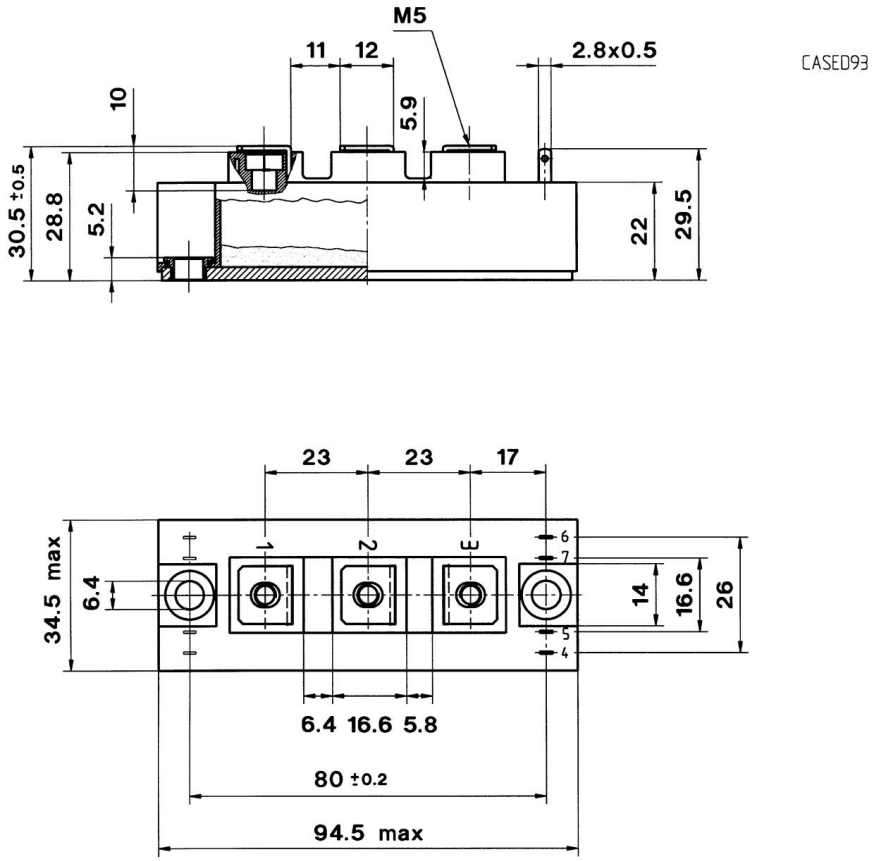
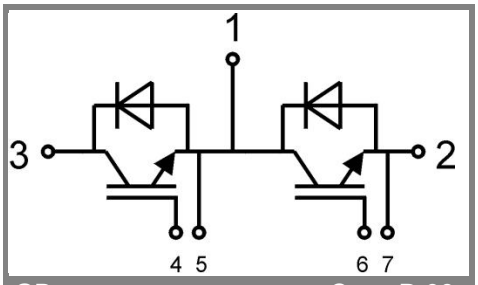


Fig. 12 Typ. CAL diode peak reverse recovery charge

UL Recognized File 63 532



Case D 93



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